

**RUC002N05**

● **Structure**

TY N-channel MOSFET

● **Features**

- 1) High speed switing.
- 2) Small package(SST3).
- 3)Ultra low voltage drive(1.2V drive).

● **Application**

Switching

● **Packaging specifications**

Type	Package	Taping
	Code	T116
	Basic ordering unit (pieces)	3000
RUC002N05		○

● **Absolute maximum ratings (Ta = 25°C)**

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	50	V	
Gate-source voltage	$V_{GSS}$	±8	V	
Drain current	Continuous	$I_D$	±200	mA
	Pulsed	$I_{DP}$ *1	±800	mA
Source current (Body Diode)	Continuous	$I_S$	150	mA
	Pulsed	$I_{SP}$ *1	800	mA
Power dissipation	$P_D$ *2	200	mW	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

\*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$

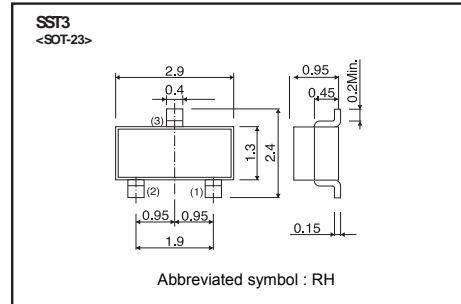
\*2 Each terminal mounted on a recommended land.

● **Thermal resistance**

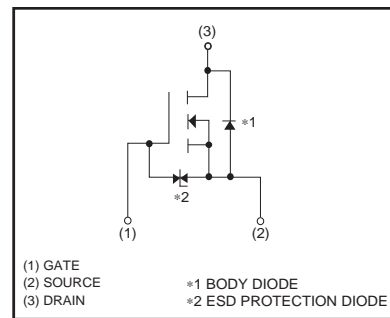
Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th}(ch-a)^*$	625	°C / W

\* Each terminal mounted on a recommended land.

● **Dimensions (Unit : mm)**



● **Inner circuit**



**● Electrical characteristics (Ta = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	$\pm 10$	$\mu A$	$V_{GS}=\pm 8V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=50V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	1.0	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	1.6	2.2	$\Omega$	$I_D=200mA, V_{GS}=4.5V$
		-	1.7	2.4		$I_D=200mA, V_{GS}=2.5V$
		-	1.9	2.7		$I_D=100mA, V_{GS}=1.8V$
		-	2.0	4.0		$I_D=40mA, V_{GS}=1.5V$
		-	2.4	7.2		$I_D=20mA, V_{GS}=1.2V$
Forward transfer admittance	$ Y_{fs} ^*$	0.4	-	-	S	$I_D=200mA, V_{DS}=10V$
Input capacitance	$C_{ISS}$	-	25	-	pF	$V_{DS}=10V$
Output capacitance	$C_{OSS}$	-	6	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{RSS}$	-	3	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	4	-	ns	$I_D=100mA, V_{DD}\approx 30V$
Rise time	$t_r^*$	-	6	-	ns	$V_{GS}=4.5V$
Turn-off delay time	$t_{d(off)}^*$	-	15	-	ns	$R_L=300\Omega$
Fall time	$t_f^*$	-	55	-	ns	$R_G=10\Omega$

\*Pulsed

**● Body diode characteristics (Source-Drain) (Ta = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}^*$	-	-	1.2	V	$I_S=200mA, V_{GS}=0V$

\*Pulsed